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What is claimed is:

1. A method of manufacturing a semiconductor device; which comprises the steps of:

depositing, on a basic substance surface with a difference in level, a first film through an anisotropic growth;

forming, through an isotropic growth, a second film having a polishing rate equivalent to or less than a polishing rate of said first film to reinforce a projection formed on said first film; and

polishing said first film and said second film using a ceria slurry.

2. A method of manufacturing a semiconductor device according to Claim 1, wherein said difference in level is formed of a trench.

3. A method of manufacturing a semiconductor device according to Claim 1, wherein said difference in level is formed of an interconnection.

4. A method of manufacturing a semiconductor device according to Claims 1, wherein a stopper film which is to act as a polishing stopper, having a polishing rate less than a polishing rate of said first film, is formed on an upper level section constituting said difference in level.

5. A method of manufacturing a semiconductor device according to Claim 4, wherein said first film and said second film are both oxide films and said stopper film is a nitride film.

6. A method of manufacturing a semiconductor device according to Claim 1, wherein said first film is a film formed by the high density plasma CVD (Chemical Vapor Deposition) method.

7. A method of manufacturing a semiconductor device according to Claim 1, wherein said second film is a film formed by one of the atmospheric CVD method, the low pressure CVD method and the plasma CVD method.

8. A method of manufacturing a semiconductor device; which